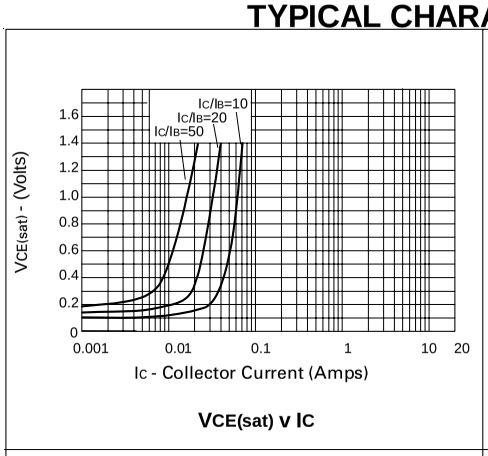
THE DATASHEET OF

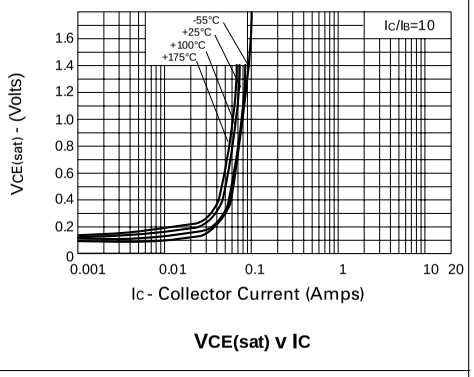
ZTX558QSTZ

ZTX558

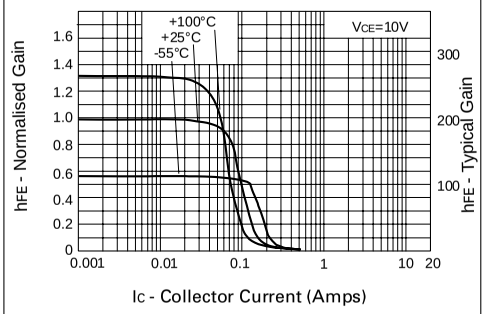
TYPICAL CHARACTERISTICS



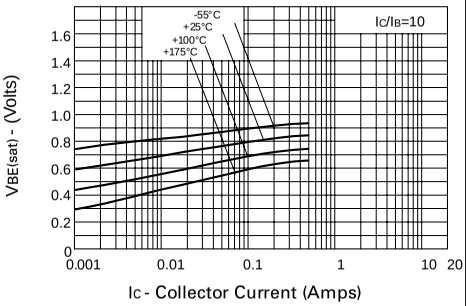
VCE(sat) v IC



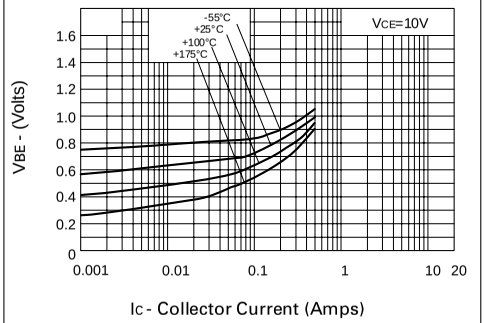
VCE(sat) v IC



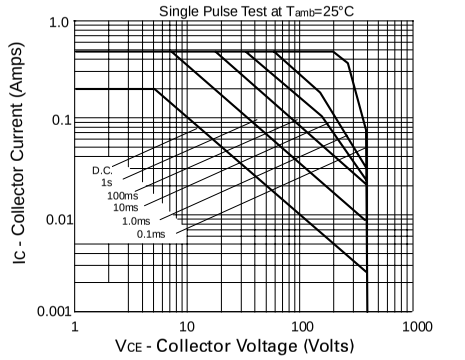
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area

PNP SILICON PLANAR ME
HIGH VOLTAGE TRANSIST

ISSUE 1 – APRIL 94

FEATURES

* 400 Volt V_{CEO}
* 200mA continuous current
* P_{tot}= 1 Watt

ABSOLUTE MAXIMUM RATINGS

PARAMETER
Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Temperature Ran

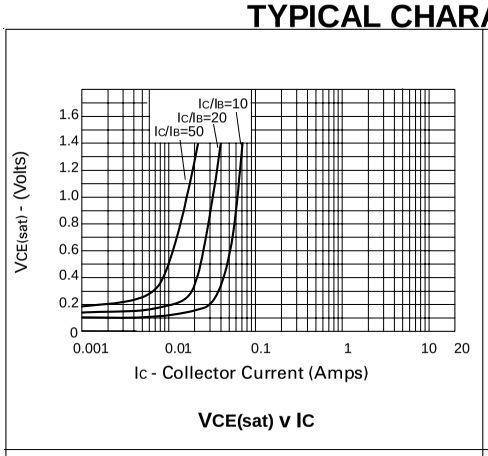
ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	MI
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-4
Collector-Emitter Breakdown Voltage	$V_{BR(CEO)}$	-4
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5
Collector Cut-Off Current	I_{CBO}	
Collector Cut-Off Current	I_{CES}	
Emitter Cut-Off Current	I_{EBO}	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	
Base-Emitter Turn On Voltage	$V_{BE(on)}$	
Static Forward Current Transfer Ratio	h_{FE}	10 10 15
Transition Frequency	f_T	50
Collector-Base Breakdown Voltage	C_{obo}	
Switching times	t_{on} t_{off}	

* Measured under pulsed conditions. Pulse

ZTX558

TYPICAL CHARACTERISTICS



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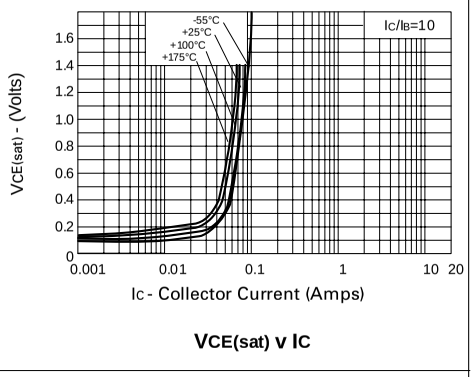

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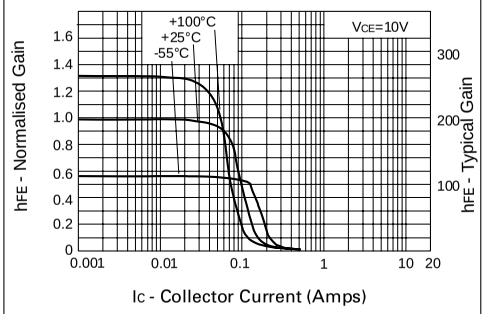

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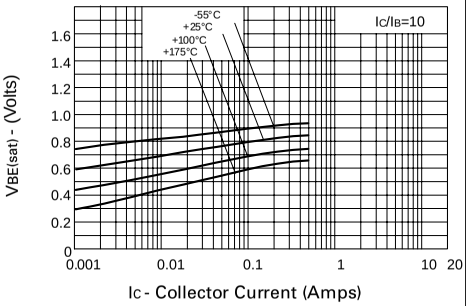
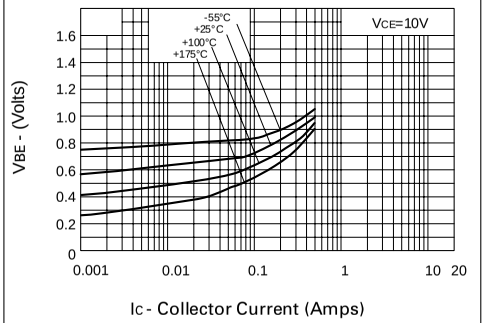
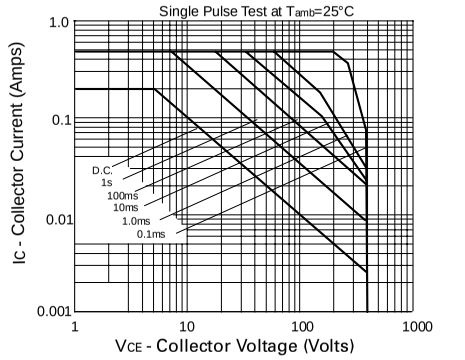


VBE(sat) v IC



VBE(on) v IC



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